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II Semester Diploma Examination, Oct./Nov.-2019

BASICS OF SEMICONDUCTOR DEVICES

Tim	e : 3 H	ours]	[Max. Marks : 100
Instr	uctions	: (i) Answer any six questions from Part – A.	$(5 \times 6 = 30 \text{ marks})$
		(ii) Answer any seven full questions from Par	$t - \mathbf{B}. \ (7 \times 10 = 70 \text{ marks})$
		PART – A	
1.	Define	the following with respect to energy bands in sol	ids: 5
	(a) \	/alance band	
	(b) (Conduction band	
	(c) F	Forbidden energy gap	
2.	Draw	and lable NPN Transistor configurations.	5
3.	Define	e Transistor. Describe terminals of the transistor.	5
4.	Expla	in working of CMOS invertor.	5
5.	Defin	e the following with respect to J.F.E.T.:	5
	(a)	Transconductance	
	(b)	Drain Resistance	
	(c)	Amplification factor	
6.	Class	ify the IC's based on structure and functions.	5 .
7.	Defin	e intrinsic standoff ratio. Mention applications of	U.J.T. 5
8.	Sumi	marise characteristics of varactor diode.	5
9.	Defin	ne:	5
	(a)	Photo emission	
	(b)	Photo conduction	
	(c)	Photo voltaic effect	
•		1 of 2	[Turn over

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PART – B

